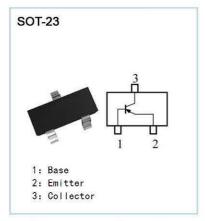




PNP Silicon Epitaxial Planar Transistor

for switching and amplifier applications. Especially suitable for AF-driver stages and low power output stages.

As complementary type the NPN transistor



Absolute Maximum Ratings (T_a = 25 °C)

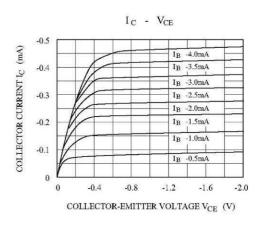
Parameter	Symbol	Value	Unit
Collector Base Voltage	-V _{CBO}	40	٧
Collector Emitter Voltage	-V _{CEO}	25	٧
Emitter Base Voltage	-V _{EBO}	6	٧
Collector Current	-lc	1.5	Α
Power Dissipation	P _{tot}	350	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	Ts	- 55 to + 150	°C

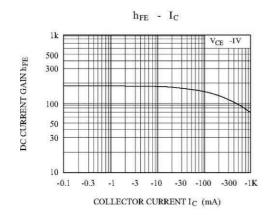
Characteristics at Ta = 25 °C

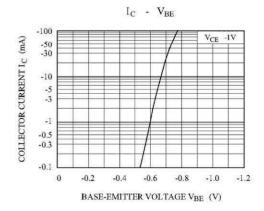
Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at -V _{CE} = 1 V, -I _C = 100 mA				
at -V _{CE} = 1 V, -I _C = 800 mA	h _{FE}	200	350	-
Collector Base Cutoff Current at -V _{CB} = 35 V	-I _{CBO}	;c=	100	nA
Emitter Base Cutoff Current at -V _{EB} = 6 V	-I _{EBO}	3	100	nA
Collector Base Breakdown Voltage at -I _C = 100 µA	-V _{(BR)CBO}	40	₩1	V
Collector Emitter Breakdown Voltage at -I _C = 2 mA	-V _{(BR)CEO}	25	-	V
Emitter Base Breakdown Voltage at -I _E = 100 μA	-V _{(BR)EBO}	6	-	V
Collector Emitter Saturation Voltage at -I _C = 800 mA, -I _B = 80 mA	-V _{CE(sat)}	.=	0.5	V
Base Emitter Saturation Voltage at -I _C = 800 mA, -I _B = 80 mA	-V _{BE(sat)}	12	1.2	V
Base Emitter Voltage at -V _{CE} = 1 V, -I _C = 10 mA	-V _{BE(on)}	Æ	1	V
Gain Bandwidth Product at -V _{CE} = 10 V, -I _C = 50 mA	f _T	120	-	MHz

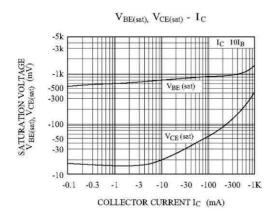


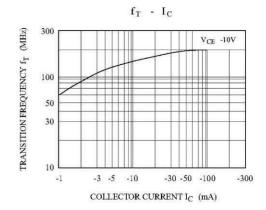


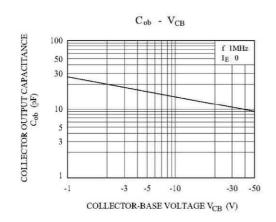
















PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23

